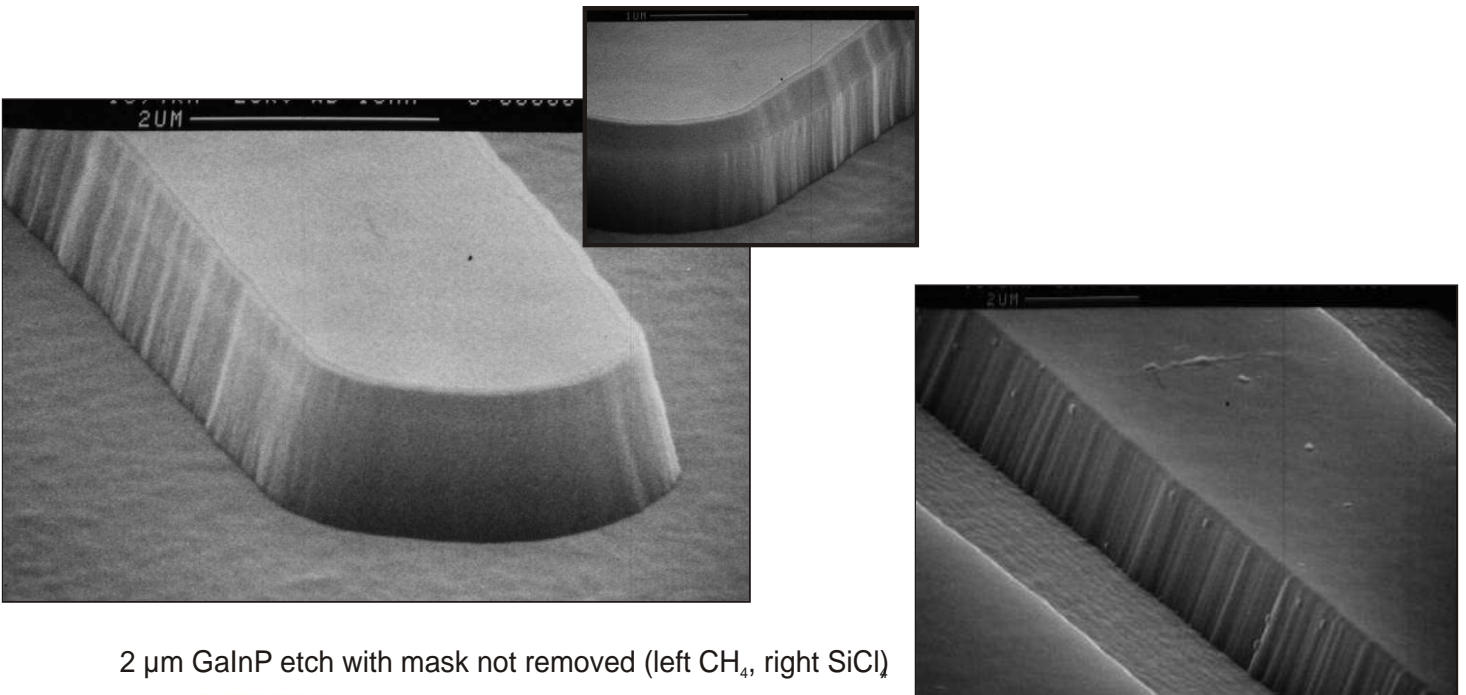


Plasmalab Data

GaInP - Reactive Ion Etching

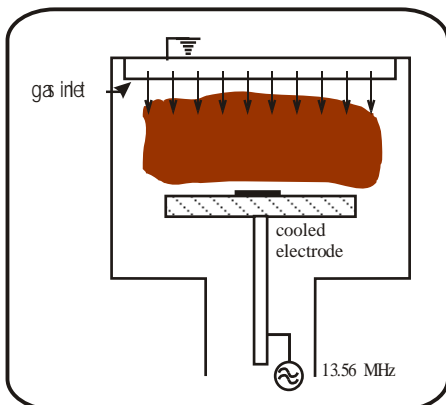


2 µm GaInP etch with mask not removed (left CH₄, right SiCl₄)



Plasmalab System 100
Plasmalab System 133

Plasmalab 80 Plus



Technology:

Parallel Plate Configuration
RIE-Mode (13.56 MHz)
Shower Head Gas Inlet

Results:

Rate : ca. 8 (CH₄) - 30 (SiCl₄) nm/ min
Mask: Photoresist or SiO₂
60° - 87° walls (depending on mask)
smoother with CH₄(mask dependent)